What is claimed is:

1.   An electroluminescence display device comprising:

a display pixel region disposed on a substrate and having

5   an electroluminescence element including an emissive layer between

first and second electrodes; and

a drive circuit region disposed on the same substrate and

having thin film transistors for driving said electroluminescence

element; wherein

10   said first electrode entirely overlaps said display pixel

region and is absent from at least said drive circuit region.

2.   The device defined in Claim 1 wherein said first electrode

is formed as a common electrode in said display pixel region.

3.   The device defined in Claim 1 wherein:

said display pixel region includes first and second thin film

transistors for driving said electroluminescence element;

an insulating film is formed overlapping said first and

20   second thin film transistors and said thin film transistors of said

drive circuit region; and

said first electrode is formed over said insulating film in

a position opposing said display pixel region.

25   4.   The device defined in Claim 3 wherein a circuit in said drive

circuit region includes a CMOS connection structure in which a

p-type channel thin film transistor and a n-type channel thin film

transistor are complementarily connected.

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5.   The device defined in Claim 1 wherein:

said thin film transistors of said drive circuit region are bottom gate type transistors having gate electrodes located beneath an active layer; and

5   said first electrode is formed over an insulating layer extending on the entire substrate on an opposite side of said active layer from which said gate electrodes are located, said first electrode formed overlapping said display pixel region.

10   6.   The device defined in Claim 1 wherein said first electrode is a common cathode, and said second electrode is a discrete anode.

7.   The device defined in Claim 6 wherein said emissive layer is a layer including an organic compound as an emissive material.

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8.   An electroluminescence display device comprising a substrate provided with:

a display pixel region having an electroluminescence element including an emissive layer between an anode and a cathode, and
20   first and second thin film transistors for driving said electroluminescence element; and

a drive circuit region disposed surrounding said display pixel region and having third thin film transistors for driving said first and second thin film transistors; wherein
25   said cathode is disposed in said display pixel region and is absent from said drive circuit region.

9.   The device defined in Claim 8 wherein said cathode on said substrate is formed over the entire display pixel region as a common

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electrode, and is absent from at least said drive circuit region.

10. The device defined in Claim 8 wherein a circuit in said drive circuit region includes a CMOS connection structure in which a p-type channel thin film transistor and a n-type channel thin film transistor are complementarily connected.

11. The device defined in Claim 8 wherein:

said third thin film transistors of said drive circuit region are bottom gate type transistors having gate electrodes located beneath an active layer; and

said cathode is formed over an insulating layer extending on the entire substrate on an opposite side of said active layer from which said gate electrodes are located, said cathode formed overlapping said display pixel region.

12. An emissive display device comprising:

a display pixel region disposed on a substrate and having an emissive element including an emissive layer between first and second electrodes; and

a drive circuit region disposed on the same substrate surrounding said display pixel region, said drive circuit region having thin film transistors for driving said emissive element; wherein

said first electrode overlaps the entire display pixel region and is absent from at least said drive circuit region.

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